Victor Ryzhii

List of Publications by Year
in descending order

180	6,289	66343	79698
papers	citations	42 h-index	73 g-index

183	183	183	2921
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Terahertz-wave generation using graphene: Toward new types of terahertz lasers. Proceedings of the IEEE, 2024, , 1-13.	21.3	1
2	Graphene-based plasmonic metamaterial for terahertz laser transistors. Nanophotonics, 2022, 11, 1677-1696.	6.0	15
3	Graphene-based plasma-wave devices for terahertz applications. , 2022, , .		0
4	Coulomb drag and plasmonic effects in graphene field-effect transistors enable resonant terahertz detection. Applied Physics Letters, 2022, 120, 111102.	3.3	3
5	Modulation characteristics of uncooled graphene photodetectors. Journal of Applied Physics, 2021, 129, .	2.5	10
6	Heat capacity of nonequilibrium electron-hole plasma in graphene layers and graphene bilayers. Physical Review B, 2021, 103, .	3.2	2
7	Dynamic characteristics of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msup><mml:mi>n</mml:mi><mml:mo>+</mml:mo></mml:msup></mml:math> - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>i</mml:mi></mml:math> - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>n</mml:mi></mml:math> graphene FETs with ballistic injection.	3.8	18
8	Coulomb electron drag mechanism of terahertz plasma instability in n+-i-n-n+ graphene FETs with ballistic injection. Applied Physics Letters, 2021, 119, .	3.3	13
9	Theoretical analysis of injection driven thermal light emitters based on graphene encapsulated by hexagonal boron nitride. Optical Materials Express, 2021, 11, 468.	3.0	8
10	Current Driven Plasma Instability in Graphene-FETs with Coulomb Electron Drag. , 2021, , .		0
11	Effect of Coulomb Carrier Drag and Terahertz Plasma Instability in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msup><mml:mi>p</mml:mi><mml:mo>+</mml:mo></mml:msup></mml:math> - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>p</mml:mi></mml:math> - <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>n</mml:mi></mml:math>	3.8	8
12	Sub-terahertz FET detector with self-assembled Sn-nanothreads. Journal Physics D: Applied Physics, 2020, 53, 075102.	2.8	7
13	Multiple graphene-layer-based heterostructures with van der Waals barrier layers for terahertz superluminescent and laser diodes with lateral/vertical current injection. Semiconductor Science and Technology, 2020, 35, 085023.	2.0	3
14	Graphene based plasma-wave devices for terahertz applications. Applied Physics Letters, 2020, 116, .	3.3	48
15	Far-infrared photodetectors based on graphene/black-AsP heterostructures. Optics Express, 2020, 28, 2480.	3.4	27
16	Far-infrared and terahertz emitting diodes based on graphene/black-P and graphene/MoS2 heterostructures. Optics Express, 2020, 28, 24136.	3.4	7
17	Far-infrared photodetection in graphene nanoribbon heterostructures with black-phosphorus base layers. Optical Engineering, 2020, 60, .	1.0	1
18	Concepts of infrared and terahertz photodetectors based on vertical graphene van der Waals and HgTe-CdHgTe heterostructures. Opto-electronics Review, 2019, 27, 219-223.	2.4	2

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19	Negative terahertz conductivity and amplification of surface plasmons in grapheneâ€“black phosphorus injection laser heterostructures. Physical Review B, 2019, 100, .	3.2	21
20	Characteristics of vertically stacked graphene-layer infrared photodetectors. Solid-State Electronics, 2019, 155, 123-128.	1.4	1
21	Negative photoconductivity and hot-carrier bolometric detection of terahertz radiation in graphene-phosphorene hybrid structures. Journal of Applied Physics, 2019, 125, 151608.	2.5	12
22	Optical Pumping of Graphene-Based Heterostructures with Black-Arsenic-Phosphorus Absorbing-Cooling Layer for Terahertz Lasing. , 2019, , .		0
23	Comment on â€œNegative Landau Damping in Bilayer Grapheneâ€• Physical Review Letters, 2019, 123, 219401.	7.8	17
24	Negative Terahertz Conductivity at Vertical Carrier Injection in a Black-Arsenic-Phosphorusâ€“Graphene Heterostructure Integrated With a Light-Emitting Diode. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-9.	2.9	4
25	Optical pumping in graphene-based terahertz/far-infrared superluminescent and laser heterostructures with graded-gap black-PxAs1â^'x absorbing-cooling layers. Optical Engineering, 2019, 59, 1.	1.0	8
26	Negative and positive terahertz and infrared photoconductivity in uncooled graphene. Optical Materials Express, 2019, 9, 585.	3.0	24
27	Optical pumping through a black-As absorbing-cooling layer in graphene-based heterostructure: thermo-diffusion model. Optical Materials Express, 2019, 9, 4061.	3.0	9
28	Vertical Hot-electron Terahertz Detectors Based on Black-As1?xPx/graphene/black-As1?yPy Heterostructures. Sensors and Materials, 2019, 31, 2271.	0.5	2
29	Lateral terahertz hot-electron bolometer based on an array of Sn nanothreads in GaAs. Journal Physics D: Applied Physics, 2018, 51, 135101.	2.8	17
30	Comparison of Intersubband Quantum-Well and Interband Graphene-Layer Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2018, 54, 1-8.	1.9	9
31	Device model for pixelless infrared image up-converters based on polycrystalline graphene heterostructures. Journal of Applied Physics, 2018, 123, 014503.	2.5	3
32	Terahertz light-emitting graphene-channel transistor toward single-mode lasing. Nanophotonics, 2018, 7, 741-752.	6.0	57
33	Electrical modulation of terahertz radiation using graphene-phosphorene heterostructures. Semiconductor Science and Technology, 2018, 33, 124010.	2.0	19
34	Real-space-transfer mechanism of negative differential conductivity in gated graphene-phosphorene hybrid structures: Phenomenological heating model. Journal of Applied Physics, 2018, 124, 114501.	2.5	15
35	Interband infrared photodetectors based on HgTeâ€“CdHgTe quantum-well heterostructures. Optical Materials Express, 2018, 8, 1349.	3.0	13
36	Auger recombination in Dirac materials: A tangle of many-body effects. Physical Review B, 2018, 97, .	3.2	42

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37	Infrared photodetectors based on graphene van der Waals heterostructures. Infrared Physics and Technology, 2017, 84, 72-81.	2.9	17
38	Dynamic Conductivity and Two-Dimensional Plasmons in Lateral CNT Networks. International Journal of High Speed Electronics and Systems, 2017, 26, 1740004.	0.7	0
39	Infrared detection and photon energy up-conversion in graphene layer infrared photodetectors integrated with LEDs based on van der Waals heterostructures: Concept, device model, and characteristics. Infrared Physics and Technology, 2017, 85, 307-314.	2.9	3
40	Effect of doping on the characteristics of infrared photodetectors based on van der Waals heterostructures with multiple graphene layers. Journal of Applied Physics, 2017, 122, .	2.5	12
41	Nonlinear response of infrared photodetectors based on van der Waals heterostructures with graphene layers. Optics Express, 2017, 25, 5536.	3.4	18
42	Plasmonic Enhancement of Terahertz Devices Efficiency. , 2017, , .		0
43	Ultra-compact injection terahertz laser using the resonant inter-layer radiative transitions in multi-graphene-layer structure. Optics Express, 2016, 24, 29603.	3.4	11
44	Plasmonic Enhancement of Terahertz Devices Efficiency. International Journal of High Speed Electronics and Systems, 2016, 25, 1640019.	0.7	0
45	Resonant plasmonic terahertz detection in graphene split-gate field-effect transistors with lateral pâ€“n junctions. Journal Physics D: Applied Physics, 2016, 49, 315103.	2.8	27
46	Enhanced Terahertz Emission from Monolayer Graphene with Metal Mesh Structure. Materials Today: Proceedings, 2016, 3, S221-S226.	1.8	0
47	Giant plasmon instability in a dual-grating-gate graphene field-effect transistor. Physical Review B, 2016, 93, .	3.2	42
48	Terahertz wave generation and detection in double-graphene layered van der Waals heterostructures. 2D Materials, 2016, 3, 045009.	4.4	56
49	Resonant plasmonic terahertz detection in vertical graphene-base hot-electron transistors. Journal of Applied Physics, 2015, 118, .	2.5	16
50	Graphene Active Plasmonics for New Types of Terahertz Lasers. , 2015, , .		1
51	Graphene vertical cascade interband terahertz and infrared photodetectors. 2D Materials, 2015, 2, 025002.	4.4	20
52	Vertical electron transport in van der Waals heterostructures with graphene layers. Journal of Applied Physics, 2015, 117, 154504.	2.5	11
53	Terahertz Wave Generation Using Graphene and Compound Semiconductor Nano-Heterostructures. Nanostructure Science and Technology, 2015, , 237-261.	0.1	0
54	Electron Capture in van der Waals Graphene-Based Heterostructures with WS₂ Barrier Layers. Journal of the Physical Society of Japan, 2015, 84, 094703.	1.6	18

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55	Negative terahertz conductivity in disordered graphene bilayers with population inversion. Applied Physics Letters, 2015, 106, 113501.	3.3	16
56	Graphene Active Plasmonics for New Types of Terahertz Lasers. International Journal of High Speed Electronics and Systems, 2014, 23, 1450016.	0.7	1
57	Carrier-carrier scattering and negative dynamic conductivity in pumped graphene. Optics Express, 2014, 22, 19873.	3.4	33
58	Graphene vertical hot-electron terahertz detectors. Journal of Applied Physics, 2014, 116, 114504.	2.5	18
59	Double injection, resonant-tunneling recombination, and current-voltage characteristics in double-graphene-layer structures. Journal of Applied Physics, 2014, 115, .	2.5	18
60	Negative dynamic Drude conductivity in pumped graphene. Applied Physics Express, 2014, 7, 115101.	2.4	12
61	Voltage-tunable terahertz and infrared photodetectors based on double-graphene-layer structures. Applied Physics Letters, 2014, 104, .	3.3	32
62	Surface-plasmons lasing in double-graphene-layer structures. Journal of Applied Physics, 2014, 115, 044511.	2.5	21
63	Active graphene plasmonics for terahertz device applications. Journal Physics D: Applied Physics, 2014, 47, 094006.	2.8	101
64	Plasma resonant terahertz photomixers based on double graphene layer structures. Journal of Physics: Conference Series, 2014, 486, 012032.	0.4	1
65	Double injection in graphene p-i-n structures. Journal of Applied Physics, 2013, 113, 244505.	2.5	32
66	Hydrodynamic electron transport and nonlinear waves in graphene. Physical Review B, 2013, 88, .	3.2	66
67	Dynamic effects in double graphene-layer structures with inter-layer resonant-tunnelling negative conductivity. Journal Physics D: Applied Physics, 2013, 46, 315107.	2.8	46
68	Injection terahertz laser using the resonant inter-layer radiative transitions in double-graphene-layer structure. Applied Physics Letters, 2013, 103, .	3.3	47
69	The gain enhancement effect of surface plasmon polaritons on terahertz stimulated emission in optically pumped monolayer graphene. New Journal of Physics, 2013, 15, 075003.	2.9	94
70	Effect of self-consistent electric field on characteristics of graphene p-i-n tunneling transit-time diodes. Journal of Applied Physics, 2013, 113, .	2.5	10
71	Emission and Detection of Terahertz Radiation Using Two-Dimensional Electrons in IIIâ€“V Semiconductors and Graphene. IEEE Transactions on Terahertz Science and Technology, 2013, 3, 63-71.	3.1	98
72	Graphene terahertz uncooled bolometers. Journal Physics D: Applied Physics, 2013, 46, 065102.	2.8	38

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73	Terahertz-Wave Generation Using Graphene: Toward New Types of Terahertz Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 8400209-8400209.	2.9	68
74	Terahertz photomixing using plasma resonances in double-graphene layer structures. Journal of Applied Physics, 2013, 113, .	2.5	47
75	Graphene active plasmonic metamaterials for new types of terahertz lasers. , 2013, , .		1
76	Graphene materials and devices for terahertz science and technology. , 2013, , .		2
77	Amplification and lasing of terahertz radiation by plasmons in graphene with a planar distributed Bragg resonator. Journal of Optics (United Kingdom), 2013, 15, 114009.	2.2	44
78	Plasmonic terahertz lasing in an array of graphene nanocavities. Physical Review B, 2012, 86, .	3.2	101
79	Double graphene-layer plasma resonances terahertz detector. Journal Physics D: Applied Physics, 2012, 45, 302001.	2.8	76
80	Graphene-based devices in terahertz science and technology. Journal Physics D: Applied Physics, 2012, 45, 303001.	2.8	234
81	Graphene materials and devices in terahertz science and technology. MRS Bulletin, 2012, 37, 1235-1243.	3.5	30
82	Terahertz and infrared photodetectors based on multiple graphene layer and nanoribbon structures. Opto-electronics Review, 2012, 20, .	2.4	53
83	Hydrodynamic model for electron-hole plasma in graphene. Journal of Applied Physics, 2012, 111, .	2.5	132
84	Ultrafast carrier dynamics and terahertz emission in optically pumped graphene at room temperature. Physical Review B, 2012, 85, .	3.2	169
85	Spectroscopic Study on Ultrafast Carrier Dynamics and Terahertz Amplified Stimulated Emission in Optically Pumped Graphene. Journal of Infrared, Millimeter, and Terahertz Waves, 2012, 33, 825-838.	2.2	12
86	Effect of Heating and Cooling of Photogenerated Electronâ€“Hole Plasma in Optically Pumped Graphene on Population Inversion. Japanese Journal of Applied Physics, 2011, 50, 094001.	1.5	35
87	Toward the creation of terahertz graphene injection laser. Journal of Applied Physics, 2011, 110, .	2.5	141
88	Terahertz surface plasmons in optically pumped graphene structures. Journal of Physics Condensed Matter, 2011, 23, 145302.	1.8	168
89	New semiconductor materials and devices for terahertz imaging and sensing. , 2011, , .		0
90	Observation of Amplified Stimulated Terahertz Emission from Optically Pumped Heteroepitaxial Graphene-on-Silicon Materials. Journal of Infrared, Millimeter, and Terahertz Waves, 2011, 32, 655-665.	2.2	41

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91	Emission of Terahertz Radiation from Two-Dimensional Electron Systems in Semiconductor Nano- and Hetero-Structures. Journal of Infrared, Millimeter, and Terahertz Waves, 2011, 32, 629-645.	2.2	26
92	Tunneling recombination in optically pumped graphene with electron-hole puddles. Applied Physics Letters, 2011, 99, .	3.3	10
93	Terahertz light amplification by stimulated emission of radiation from optically pumped graphene. Proceedings of SPIE, 2011, , .	0.8	6
94	Theoretical Study of Population Inversion in Graphene under Pulse Excitation. Japanese Journal of Applied Physics, 2011, 50, 070116.	1.5	19
95	Terahertz Amplifiers based on Multiple Graphene Layer with Field-Enhancement Effect. Japanese Journal of Applied Physics, 2011, 50, 070118.	1.5	4
96	Effect of Heating and Cooling of Photogenerated Electronâ€“Hole Plasma in Optically Pumped Graphene on Population Inversion. Japanese Journal of Applied Physics, 2011, 50, 094001.	1.5	37
97	Oblique terahertz plasmons in graphene nanoribbon arrays. Physical Review B, 2010, 81, .	3.2	74
98	Negative terahertz dynamic conductivity in electrically induced lateral pâ€“iâ€“n junction in graphene. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 719-721.	2.7	9
99	Electrically induced<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>n</mml:mi><mml:mtext>â^’</mml:mtext><mml:mi>i</mml:mi><mml:mtext>â^’</mml:mtext><mml:mi>n</mml:mi></mml:mrow></mml:math>in multiple graphene layer structures. Physical Review B, 2010, 82, .	3.2	26
100	Terahertz and infrared photodetection using p-i-n multiple-graphene-layer structures. Journal of Applied Physics, 2010, 107, .	2.5	73
101	Terahertz lasers based on optically pumped multiple graphene structures with slot-line and dielectric waveguides. Journal of Applied Physics, 2010, 107, .	2.5	134
102	Carrier heating in intrinsic graphene by a strong dc electric field. Physical Review B, 2009, 79, .	3.2	29
103	Terahertz Laser with Optically Pumped Graphene Layers and Fabriâ€“Perot Resonator. Applied Physics Express, 2009, 2, 092301.	2.4	77
104	Feasibility of terahertz lasing in optically pumped epitaxial multiple graphene layer structures. Journal of Applied Physics, 2009, 106, .	2.5	125
105	Nanomechanical systems with plasmonic resonances as detectors of modulated terahertz radiation. , 2009, , .		0
106	Combined resonance and resonant detection of modulated terahertz radiation in a micromachined high-electron mobility transistor. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 277-281.	0.8	6
107	Electrical excitation of shock and solitonâ€like waves in highâ€electronâ€mobility transistor structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 61-65.	0.8	6
108	Thermionic and tunneling transport mechanisms in graphene fieldâ€effect transistors. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1527-1533.	1.8	22

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109	Effect of the Coulomb scattering on graphene conductivity. JETP Letters, 2008, 88, 322-325.	1.4	21
110	Current-voltage characteristics of a graphene-nanoribbon field-effect transistor. Journal of Applied Physics, 2008, 103, .	2.5	42
111	Plasma mechanisms of resonant terahertz detection in a two-dimensional electron channel with split gates. Journal of Applied Physics, 2008, 103, .	2.5	23
112	Population inversion of photoexcited electrons and holes in graphene and its negative terahertz conductivity. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 261-264.	0.8	18
113	Photoconductivity of intrinsic graphene. Physical Review B, 2008, 77, .	3.2	81
114	Tunneling Currentâ€"Voltage Characteristics of Graphene Field-Effect Transistor. Applied Physics Express, 2008, 1, 013001.	2.4	24
115	Nonequilibrium carriers in intrinsic graphene under interband photoexcitation. Physical Review B, 2008, 78, .	3.2	53
116	Mechanism of self-excitation of terahertz plasma oscillations in periodically double-gated electron channels. Journal of Physics Condensed Matter, 2008, 20, 384207.	1.8	30
117	Broadband Terahertz Emission from Dual-Grating Gate HEMT's-Mechanism and Emission Spectral Profile. , 2008, , .		1
118	PLASMA WAVES IN TWO-DIMENSIONAL ELECTRON SYSTEMS AND THEIR APPLICATIONS. Selected Topics in Electornics and Systems, 2008, , 77-94.	0.2	1
119	RESONANT TERAHERTZ DETECTION ANTENNA UTILIZING PLASMA OSCILLATIONS IN LATERAL SCHOTTKY DIODE. Selected Topics in Electornics and Systems, 2008, , 95-102.	0.2	0
120	Plasma waves in graphene-based heterostructures and their terahertz device applications. , 2007, , .		0
121	Injection and Population Inversion in Electrically Induced pâ€"n Junction in Graphene with Split Gates. Japanese Journal of Applied Physics, 2007, 46, L151-L153.	1.5	104
122	RESONANT TERAHERTZ DETECTION ANTENNA UTILIZING PLASMA OSCILLATIONS IN LATERAL SCHOTTKY DIODE. International Journal of High Speed Electronics and Systems, 2007, 17, 539-546.	0.7	2
123	PLASMA WAVES IN TWO-DIMENSIONAL ELECTRON SYSTEMS AND THEIR APPLICATIONS. International Journal of High Speed Electronics and Systems, 2007, 17, 521-538.	0.7	11
124	Voltage and temperature dependencies of conductivity in gated graphene. Physical Review B, 2007, 76, .	3.2	141
125	Plasma waves in two-dimensional electron-hole system in gated graphene heterostructures. Journal of Applied Physics, 2007, 101, 024509.	2.5	213
126	Negative dynamic conductivity of graphene with optical pumping. Journal of Applied Physics, 2007, 101, 083114.	2.5	331

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127	Plasma effects in lateral Schottky junction tunneling transit-time terahertz oscillator. Journal of Physics: Conference Series, 2006, 38, 228-233.	0.4	13
128	Terahertz Plasma Waves in Gated Graphene Heterostructures. Japanese Journal of Applied Physics, 2006, 45, L923-L925.	1.5	117
129	Plasma Instability and Terahertz Generation in HEMTs Due to Electron Transit-Time Effect. IEICE Transactions on Electronics, 2006, E89-C, 1012-1019.	0.6	38
130	Transit-time mechanism of plasma instability in high electron mobility transistors. Physica Status Solidi A, 2005, 202, R113-R115.	1.7	39
131	Millimeter wave emission from GaN high electron mobility transistor. Applied Physics Letters, 2004, 84, 70-72.	3.3	67
132	Comparison of dark current, responsivity and detectivity in different intersubband infrared photodetectors. Semiconductor Science and Technology, 2004, 19, 8-16.	2.0	83
133	Characteristics of integrated QWIP-HBT-LED up-converter. IEEE Transactions on Electron Devices, 2003, 50, 2378-2387.	3.0	12
134	Tunnelling effects in concentric disk quantum dots: discrete - discrete and discrete - continuum limits. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1540-1543.	0.8	0
135	Plasma and transit-time mechanisms of the terahertz radiation detection in high-electron-mobility transistors. Semiconductor Science and Technology, 2003, 18, 460-469.	2.0	65
136	Plasma Wave Electronics. International Journal of High Speed Electronics and Systems, 2003, 13, 575-600.	0.7	52
137	Device Model of Integrated QWIP-HBT-LED Pixel for Infrared Focal Plane Arrays. , 2002, , .		4
138	Device model for quantum dot infrared photodetectors and their dark-current characteristics. Semiconductor Science and Technology, 2001, 16, 331-338.	2.0	79
139	Negative differential photoconductivity in quantum-dot infrared photodetectors. Applied Physics Letters, 2001, 78, 3346-3348.	3.3	29
140	Physical model and analysis of quantum dot infrared photodetectors with blocking layer. Journal of Applied Physics, 2001, 89, 5117-5124.	2.5	33
141	High-frequency performance of lateral p-n junction photodiodes. IEEE Journal of Quantum Electronics, 2001, 37, 830-836.	1.9	9
142	Nonlocal Hot-Electron Transport and Capture Model for Multiple Quantum Well Structures Excited by Infrared Radiation. Japanese Journal of Applied Physics, 2001, 40, 513-517.	1.5	8
143	On the detectivity of quantum-dot infrared photodetectors. Applied Physics Letters, 2001, 78, 3523-3525.	3.3	75
144	Monte Carlo modeling of transient recharging processes in quantum-well infrared photodetectors. IEEE Transactions on Electron Devices, 2000, 47, 1935-1942.	3.0	9

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145	Resonant Detection and Frequency Multiplication in Barrier-Injection Heterostructure Transistors. Japanese Journal of Applied Physics, 2000, 39, 4727-4732.	1.5	11
146	Periodic electric-field domains in optically excited multiple-quantum-well structures. Physical Review B, 2000, 61, 2742-2748.	3.2	26
147	Phenomenological theory of electric-field domains induced by infrared radiation in multiple quantum well structures. Physical Review B, 2000, 62, 7268-7274.	3.2	20
148	Nonlinear dynamics of recharging processes in multiple quantum well structures excited by infrared radiation. Physical Review B, 2000, 62, 10292-10296.	3.2	10
149	Analysis of photon recycling in light emitting diodes with nonuniform injection. Journal of Applied Physics, 2000, 88, 3613-3617.	2.5	9
150	Contact and Space-Charge Effects in Quantum Well Infrared Photodetectors. Japanese Journal of Applied Physics, 1999, 38, 5815-5822.	1.5	32
151	Terahertz operation of quantum-well intersubband hot-electron phototransistors. IEEE Journal of Quantum Electronics, 1999, 35, 928-935.	1.9	5
152	Photon mechanism of image smearing in integrated QWIP-LED pixelless devices. IEEE Journal of Quantum Electronics, 1999, 35, 1693-1696.	1.9	15
153	Impact of transit-time and capture effects on high-frequency performance of multiple quantum-well infrared photodetectors. IEEE Transactions on Electron Devices, 1998, 45, 293-298.	3.0	26
154	High-frequency performance of single quantum well infrared photodetectors at high power densities. IEEE Transactions on Electron Devices, 1998, 45, 1797-1803.	3.0	13
155	Terahertz response of metal-semiconductor-metal photodetectors. Journal of Applied Physics, 1998, 84, 6419-6425.	2.5	7
156	Monte Carlo analysis of ultrafast electron transport in quantum well infrared photodetectors. Applied Physics Letters, 1998, 72, 842-844.	3.3	37
157	Photoconductivity nonlinearity at high excitation power in quantum well infrared photodetectors. Applied Physics Letters, 1997, 70, 414-416.	3.3	67
158	Characteristics of quantum well infrared photodetectors. Journal of Applied Physics, 1997, 81, 6442-6448.	2.5	80
159	Voltage tunable plasma resonances in induced-base hot-electron transistors. Applied Physics Letters, 1997, 70, 2532-2534.	3.3	11
160	High-Frequency Response of Intersubband Infrared Photodetectors with a Multiple Quantum Well Structure. Japanese Journal of Applied Physics, 1997, 36, 2596-2600.	1.5	15
161	Unusual capacitance behavior of quantum well infrared photodetectors. Applied Physics Letters, 1997, 70, 1828-1830.	3.3	77
162	Analysis of integrated quantum-well infrared photodetector and light-emitting diode for implementing pixelless imaging devices. IEEE Journal of Quantum Electronics, 1997, 33, 1527-1531.	1.9	40

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163	The theory of quantum-dot infrared phototransistors. Semiconductor Science and Technology, 1996, 11, 759-765.	2.0	303
164	Injection Lasers With a Resonant-Tunneling Controlling Structure. , 1996, , .		0
165	High-frequency operation of lateral hot-electron transistors. IEEE Transactions on Electron Devices, 1995, 42, 166-171.	3.0	17
166	Contact and distributed effects in quantum well infrared photodetectors. Applied Physics Letters, 1995, 67, 3147-3149.	3.3	94
167	Electron density modulation effect in a quantumâ€well infrared phototransistor. Journal of Applied Physics, 1995, 78, 1214-1218.	2.5	32
168	Procedure for fitting Monte Carlo calculated impact ionization coefficient to experiment. Journal of Applied Physics, 1994, 76, 1672-1675.	2.5	6
169	Monte Carlo study of electron transport in strained siliconâ€carbon alloy. Journal of Applied Physics, 1994, 76, 1924-1926.	2.5	30
170	High-frequency characteristics of a quantum well diode. , 0, , .		0
171	Computer modeling of static and dynamic behavior of multiple quantum well infrared photodetectors. , 0, , .		0
172	Intersubband infrared phototransistors with a quantum-wire base. , 0, , .		0
173	Optical Tuning Of Plasma Resonances In Hot-electron Transistors. , 0, , .		0
174	Plasma waves excitation in the base of lateral hot electron transistor. , 0, , .		0
175	Subterahertz detection by high electron mobility transistors at large forward gate bias. , 0, , .		3
176	Plasma wave electronics devices. , 0, , .		1
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